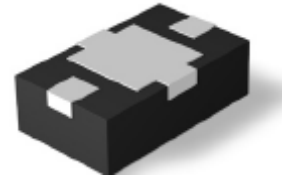


### Features

- Supports up to 40 W Power
- Low Insertion Loss:
  - 0.2 dB @ 2.7 GHz
  - 0.4 dB @ 8.0 GHz
- High Isolation:
  - 55 dB to 2.7 GHz
- RoHS\* Compliant



(2615)  
Molded Plastic DFN

### Description

A broadband, high linearity, medium power shunt switch element in a 2.6 x 1.5 mm DFN package.

This PIN diode switch element is designed for wireless telecommunications infrastructure and test instrument applications. It is also suited for other applications in 0.05 ~ 10 GHz.

### Electrical Specifications: $T_A = +25^\circ\text{C}$

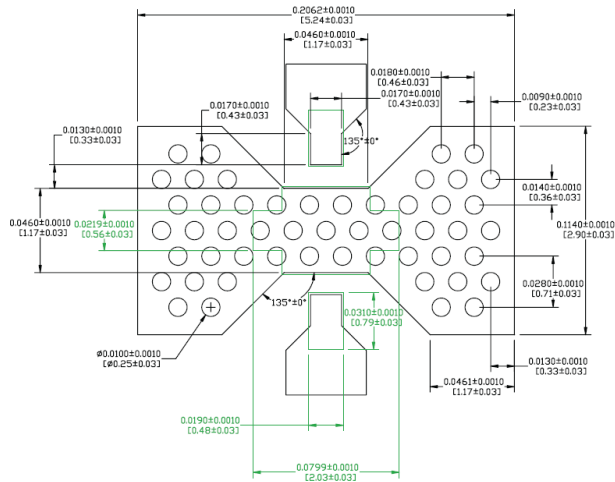
Parameter	Test Conditions	Units	Min.	Typ.	Max.
Breakdown Voltage ( $V_B$ )	$I_R = 10 \mu\text{A}$	V	300	—	—
Insertion Loss ( $I_L$ )	$V_R = 50 \text{ V}$ 2.3 - 2.7 GHz <6.0 GHz	dB	—	0.20 0.40	0.30 0.50
Isolation ( $I_{SO}$ )	$V_R = -10 \text{ V}$ 2.3 - 2.7 GHz <6.0 GHz	dB	50 35	55 40	—
Input / Output Return Loss ( $R_L$ )	$I_F = 100 \text{ mA}$ 2.3 - 2.7 GHz <6.0 GHz	dB	20 14	25 16	—
Minority Carrier Lifetime ( $T_L$ )	$I_F = 10 \text{ mA}$ , $I_R = 6 \text{ mA}$ , @ 50%	ns	—	3000	—

### Absolute Maximum Ratings

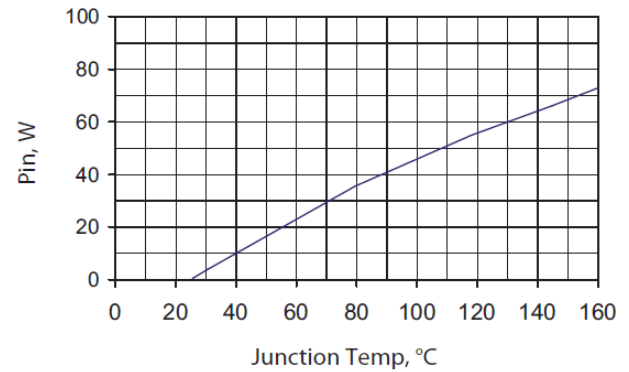
Parameter	Absolute Maximum
Breakdown Voltage	300 V
Forward Current	200 mA
Thermal Resistance	9°C/W
Junction Temperature	+175°C
Storage Temperature	-65°C to +150°C
Assembly Temperature	+260°C, Per JEDEC STD-J-20C

1 \* Restrictions on Hazardous Substances, European Union Directive 2011/65/EU.

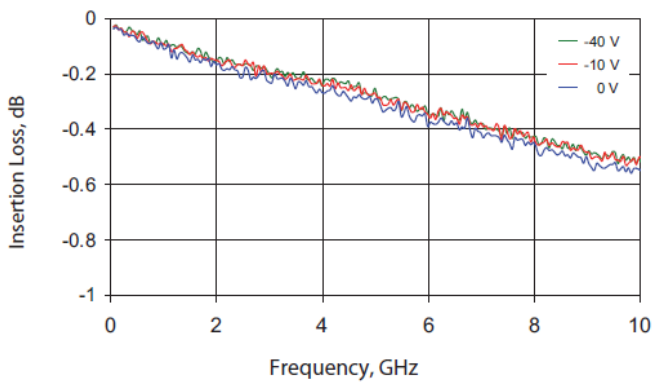
### Printed Circuit Board Layout



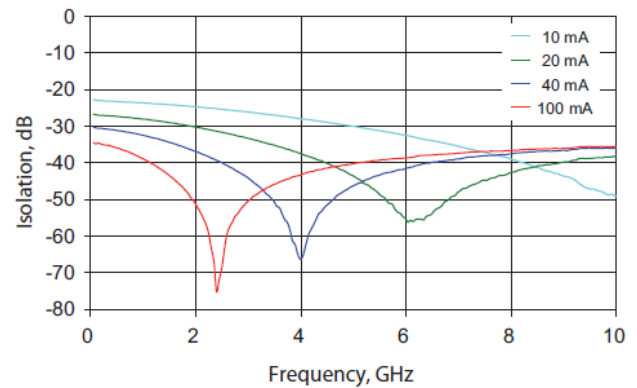
**Junction Temperature vs. Power  
Mounted on Heatsink, +25°C, 1.3 GHz**



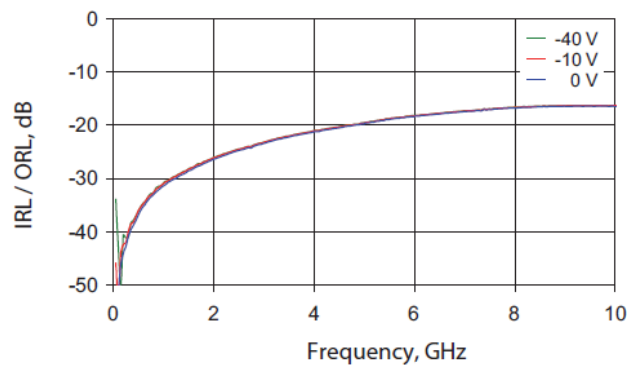
### Insertion Loss



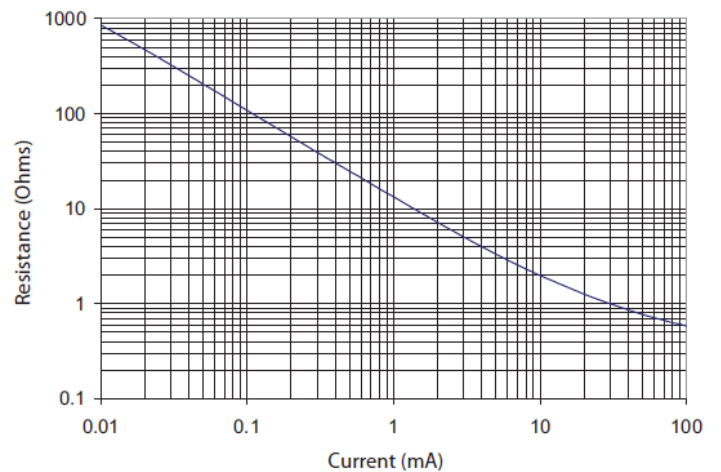
### Isolation<sup>1</sup>



### Input Return Loss



### Series Resistance vs. Bias, 500 MHz



1. Resonant frequencies vary with PCB layout. This performance measured on 20 mils Rogers RO3006 and with the printed circuit board layout shown above.

### Outline (2615)

